**Product data sheet** 

# 1. General description

Dual ultrafast power diodes in a TO3PF plastic package.

### 2. Features and benefits

- Very low on-state loss
- · Reduces switching losses in associated MOSFET or IGBT
- Low leakage current
- Isolated plastic package

# 3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	V	Values		Unit
Absolute	maximum rating					
$V_R$	repetitive peak reverse voltage	DC		600		V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; $T_h \le 96$ °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		15		А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 $\mu$ s; $T_h \le$ 96 °C; square-wave pulse; per diode	30			А
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	150			А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	165			А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	1.8	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 6</u>	-	1.3	1.6	V
Dynamic	characteristics	'	l			
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode } \frac{\text{Fig. } 7}{\text{C}}$	-	25	50	ns
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode Fig. 7	-	69	-	ns
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; per diode Fig. 7	-	100	-	ns

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	o O o	
2	K	cathode	 ⊚ O <sub>◎</sub>	A1   A2
3	A2	anode 2		K sym125
mb	n.c.	mounting base; isolated		sym125

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV415J-600P	TO3PF	BYV415J-600PQ	Tube	30	SOT1293	16-Mar-2006

# 7. Marking

### **Table 4. Marking codes**

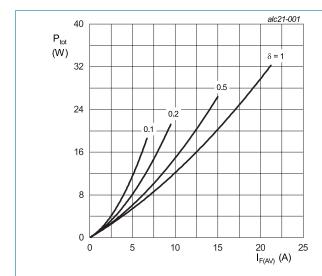
Type number	Marking codes
BYV415J-600P	BYV415J-600P

# 8. Limiting values

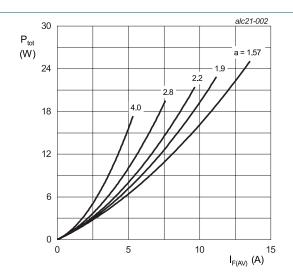
#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak reverse voltage		600	V
crest working reverse voltage		600	V
reverse voltage	DC	600	V
average forward current	δ = 0.5; T <sub>n</sub> ≤ 96 °C; square-wave pulse; per diode; <u>Fig. 1; Fig. 2; Fig. 3</u>	15	А
repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>h</sub> ≤ 96 °C; square-wave pulse; per diode	30	Α
non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	150	А
	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	165	Α
storage temperature		-65 to 175	°C
junction temperature		175	°C
	repetitive peak reverse voltage  crest working reverse voltage  reverse voltage  average forward current  repetitive peak forward current  non-repetitive peak forward current  storage temperature	$ \begin{array}{c} \text{repetitive peak reverse} \\ \text{voltage} \\ \\ \text{crest working reverse} \\ \text{voltage} \\ \\ \text{reverse voltage} \\ \\ \text{average forward current} \\ \\ \text{average forward current} \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \\ \text{observed} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	$ \begin{array}{c} \text{repetitive peak reverse} \\ \text{voltage} \\ \\ \text{crest working reverse} \\ \text{voltage} \\ \\ \text{reverse voltage} \\ \\ \text{DC} \\ \text{average forward current} \\ \\ \text{average forward current} \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \text{observed} \\ \\ \\ \text{observed}$



$$\begin{split} & |_{\text{F(AV)}} = |_{\text{F(RMS)}} \times \sqrt{\delta} \\ & |_{\text{O}} = 0.943 \text{ V; R}_{\text{s}} = 0.0273 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 0.943 V;  $R_s$  = 0.0273  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

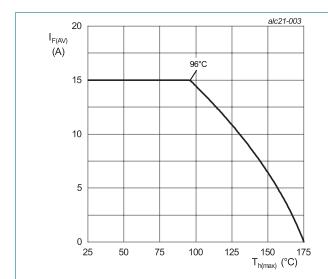


Fig. 3. Average forward current as a function of heatsink temperature; maximum values; per diode

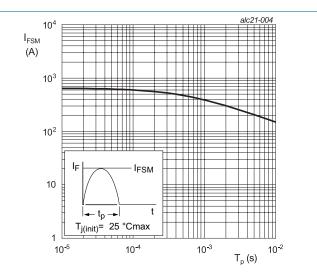


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	3	K/W
	heatsink	with heatsink compound; both diodes conducting	-	-	2.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

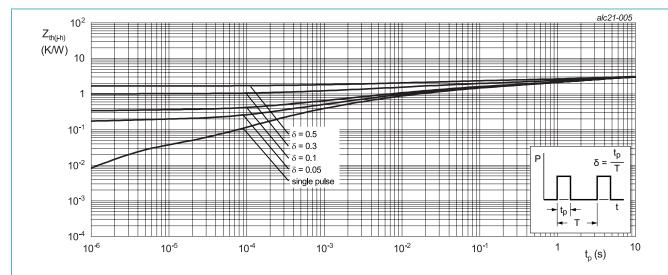


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values; per diode

### 10. Isolation characteristics

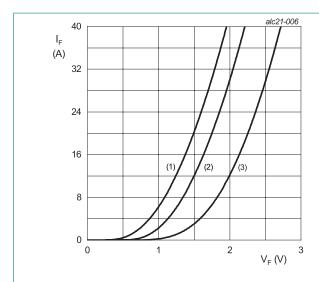
### **Table 7. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink	-	10	-	рF

## 11. Characteristics

#### **Table 8. Characteristics**

	naracteristics	0	2.41	-		11.24
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{F}$	forward voltage	$I_F = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 6$	-	1.8	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 6</u>	-	1.3	1.6	V
I <sub>R</sub>	reverse current	$V_R = 600 \text{ V}$ ; per diode; $T_j = 25 \text{ °C}$	-	-	10	μA
		V <sub>R</sub> = 600 V; per diode; T <sub>j</sub> = 150 °C	-	-	500	μA
Dynamic	characteristics			'		
t <sub>rr</sub> rev	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	25	50	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 7$	-	69	-	ns
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; per diode; Fig. 7	-	100	-	ns
$I_{RM}$	peak reverse recovery current	$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 7	-	3.5	-	А
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; per diode; Fig. 7	-	7.6	-	А
Q <sub>r</sub>	recovered charge	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 7$	-	120	-	nC
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; per diode; Fig. 7	-	380	-	nC



(1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values  $V_o$  = 0.943 V;  $R_s$  = 0.0273  $\Omega$ 

Fig. 6. Forward current as a function of forward voltage, per diode

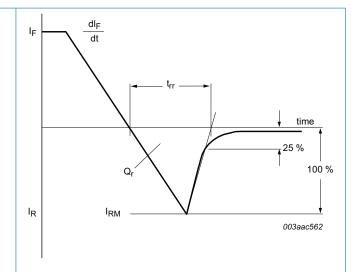
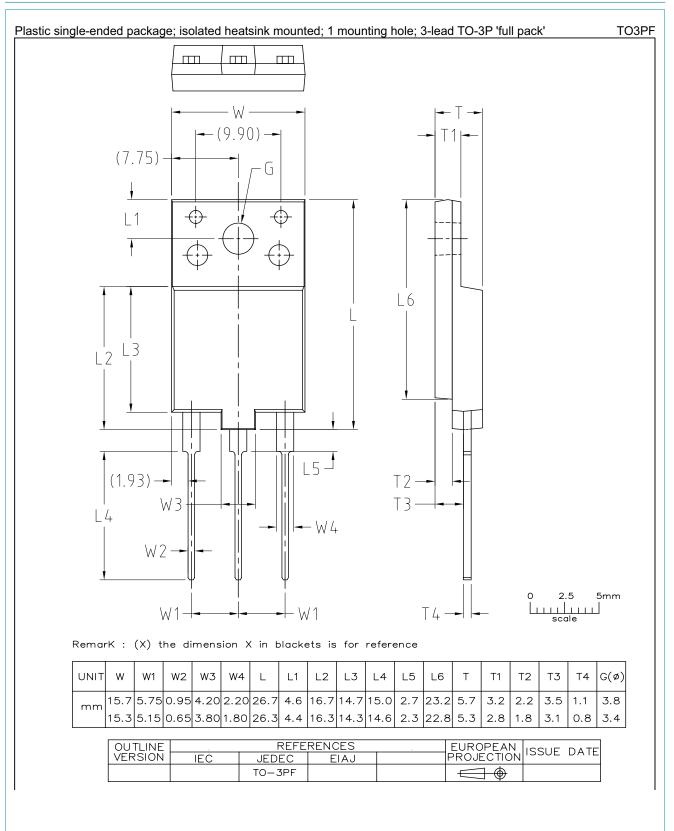


Fig. 7. Reverse recovery definitions; ramp recovery

# 12. Package outline



## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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